EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3650445	memory or storage	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/24 14:03
L2	636971	1 and (read adj only or $3rom or flash or nonvolatile or non-volatile)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/24 14:11
L3	1177	2 and select$5 near3 transistor with drain with layer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/24 14:13
L4	822	3 and source with (bit or bitline)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/24 14:06
L5	22	4 and resist$5 near3 layer with (chang$5 or var$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/24 14:07
L6	558518	1 and (read adj only or $3rom or flash)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/24 14:11
L7	984	6 and select$5 near3 transistor with drain with layer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/24 14:35
L8	6	6 and select$5 near3 transistor with drain with layer with (voltage or potential or current) with resist$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/24 14:14
L9	27933	6 and source with (bit or bitline)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/24 14:18
L10	2	8 and layer with resist$5 with (chang$5 or var$5) with (voltage or current)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/24 14:19
L11	124	9 and layer with resist$5 with (chang$5 or var$5) with (voltage or current)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/24 14:20

L12	124	11 and source with (bit or bitline)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/24 14:21
L13	16	12 and 7	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/24 14:21
L14	720	7 and source with (bit or bitline)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/24 14:35
L15	64	14 and drain with resist$5 with (voltage or potential or current)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/24 14:36